

500V 18A N-Channel Enhancement Mode Power MOSFET

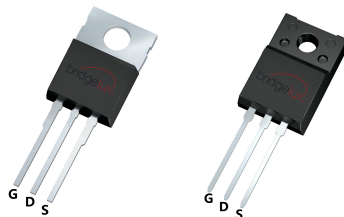
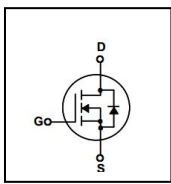
General Description

BXP18N50 is Bridgelux high voltage MOSFET family based on advanced planar DMOS technology. This advanced MOSFET family has optimized on-state resistance, and also provides superior switching performance and higher avalanche energy strength. This device family is suitable for high efficiency switch mode power supplies.

FEATURES

- $R_{DS(ON)} \leq 0.38 \Omega$ @ $V_{GS}=10V, I_D=9A$
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Fast switching capability
- Lead free product is acquired

SYMBOL



TO-220

TO-220F

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXP18N50P	TO-220	Tube
BXP18N50F	TO-220F	Tube

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating		Unit
		BXP18N50P	BXP18N50F	
Drain-Source Voltage	V_{DSS}	500		V
Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	18		A
		12		A
Drain Current	Pulsed (Note1)	72		A
Gate-Source Voltage	V_{GSS}	± 30		V
Avalanche Energy	Single Pulse (Note2)	986		mJ
Avalanche Current (Note1)	I_{AR}	18		A
Peak Diode Recovery dv/dt (Note3)	dv/dt	5		V/ns
Power Dissipation (Note 2)	$T_C = 25^\circ\text{C}$	189	42.8	W
	Derate above 25°C	1.512	0.342	W/ $^\circ\text{C}$
Maximum Junction Temperature	T_J	150		$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150		$^\circ\text{C}$

- Note:**
1. Repetitive Rating: Pulse width limited by maximum junction temperature
 2. $L=10\text{mH}$, $V_{DD}=50\text{V}$, $R_G=25 \Omega$, Starting $T_J = 25^\circ\text{C}$
 3. $I_{SD} \leq 18.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

THERMAL CHARACTERISTICS

Parameter	Symbol	Max.		Unit
		BXP18N50P	BXP18N50F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.66	2.92	$^{\circ}C / W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62.5	$^{\circ}C / W$

ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}C$, unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	500			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$			1	μA	
		$V_{DS}=400V, T_C = 125^{\circ}C$			100	μA	
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=30V$			100	nA	
Gate-Body Leakage Current, Reverse		$V_{GS}=-30V$			-100	nA	
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250 \mu A$		0.36		$V/^{\circ}C$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=9A$		0.32	0.38	Ω	
Forward Transconductance (Note4)	g_{FS}	$V_{DS} = 15V, I_D=9A$		16		S	
DYNAMIC PARAMETERS							
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$		2115		pF	
Output Capacitance	C_{OSS}				260		pF
Reverse Transfer Capacitance	C_{RSS}				20		pF
SWITCHING PARAMETERS							
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250V, I_D=18A, V_{GS} = 10V, R_G=10\Omega$ (Note4,5)		30		ns	
Turn-ON Rise Time	t_R			45		ns	
Turn-OFF Delay Time	$t_{D(OFF)}$			61		ns	
Turn-OFF Fall-Time	t_F			48		ns	
Total Gate Charge(Note5)	Q_G	$V_{DS} = 400V, V_{GS} = 10V, I_D = 18A$ (Note4,5)		45		nC	
Gate Source Charge	Q_{GS}			12		nC	
Gate Drain Charge	Q_{GD}			15		nC	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=18A, V_{GS}=0V$			1.4	V	
Diode Continuous Forward Current	I_S				18	A	
Pulsed Drain-Source Current	I_{SM}				72	A	
Reverse Recovery Time	t_{RR}	$V_{GS} = 0 V, I_{SD} = 18A$		435		ns	
Reverse Recovery Charge	Q_{RR}	$di/dt=100 A/\mu s$ (Note4,5)		4.7		μC	

Note: 4. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

5. Essentially independent of operating temperature

TYPICAL CHARACTERISTICS

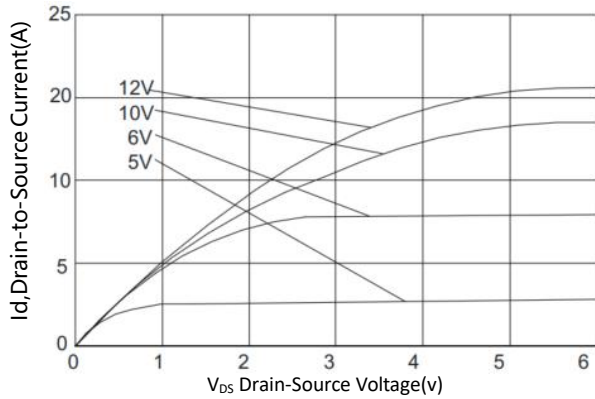


Figure1. Typical Output Characteristics

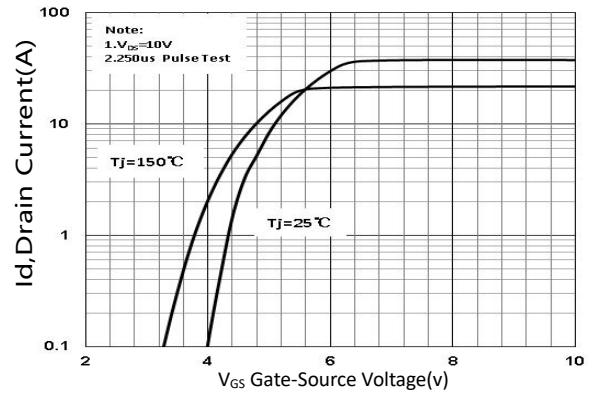


Figure2. Typical Transfer Characteristics

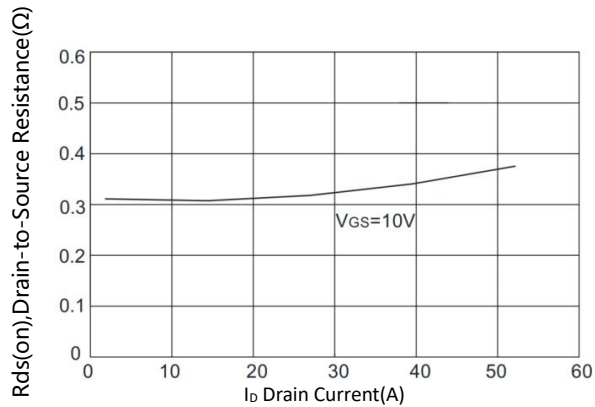


Figure3. On-Resistance versus Drain Current

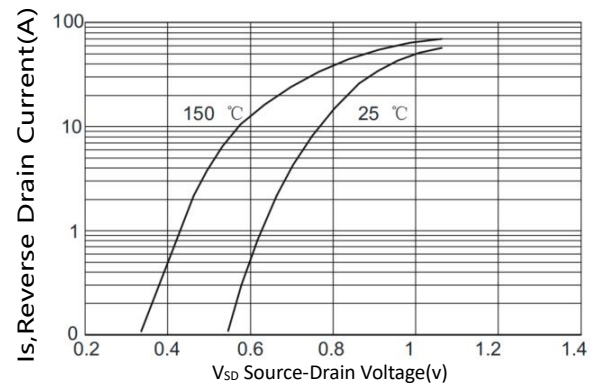


Figure4. Diode forward voltage versus Current

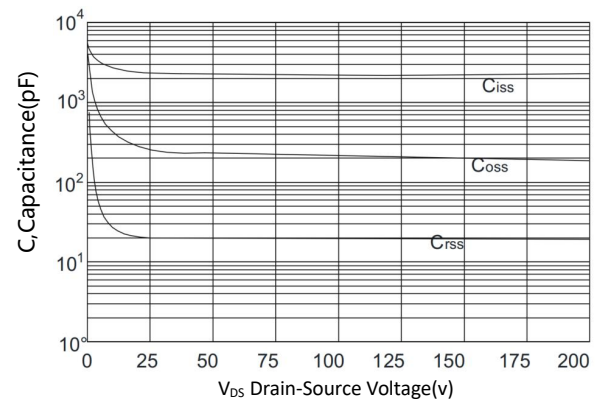


Figure5. Typical Capacitance versus VDS

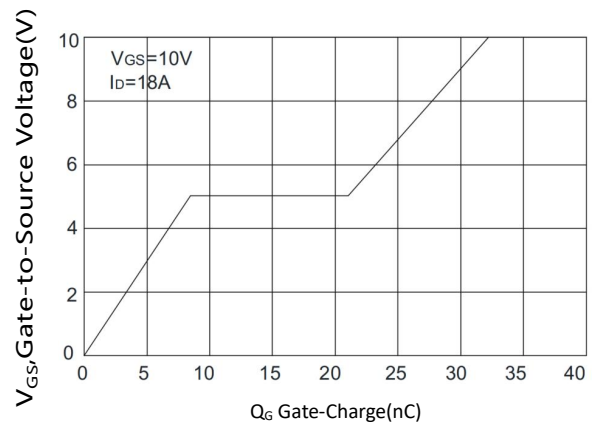


Figure6. Typical Gate Charge versus VGS

TYPICAL CHARACTERISTICS(Cont.)

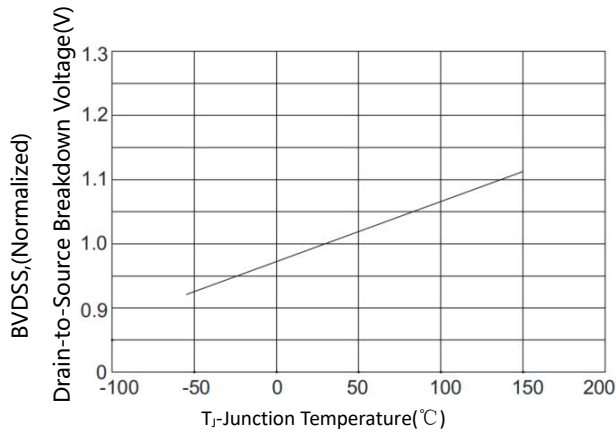


Figure7. BV_{DSS} Variation with Temperature

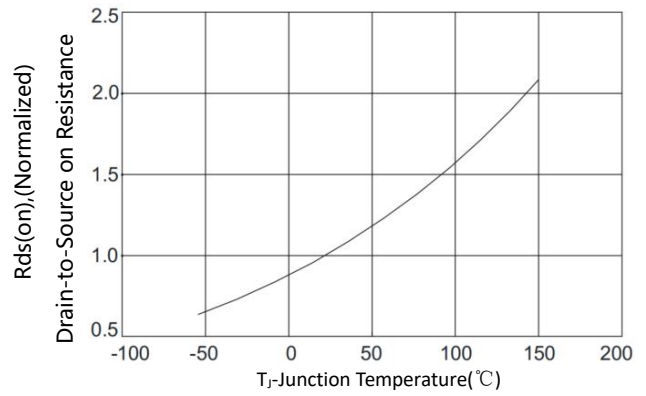
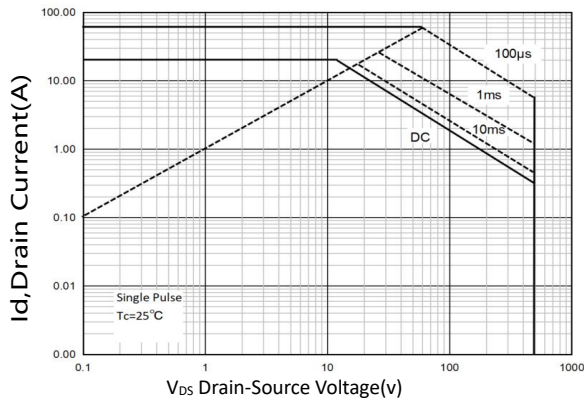
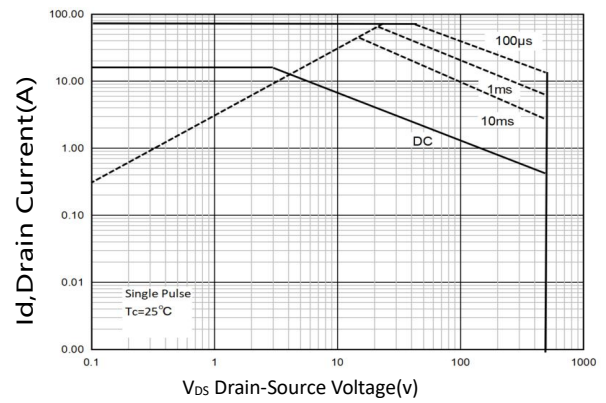


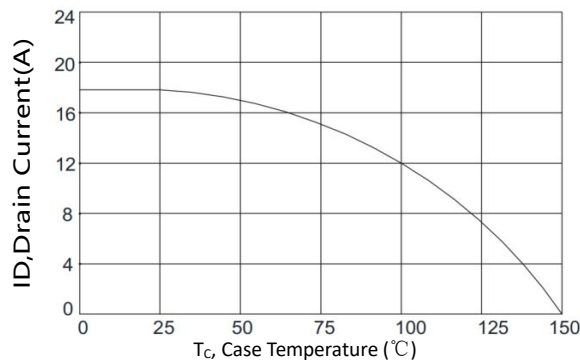
Figure8. On-Resistance Variation with Temperature



**Figure9. Maximum Safe Operating Area
BXP18N50P**

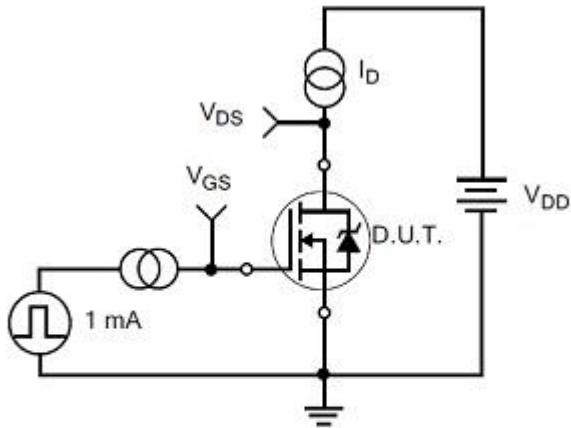


**Figure9. Maximum Safe Operating Area
BXP18N50F**

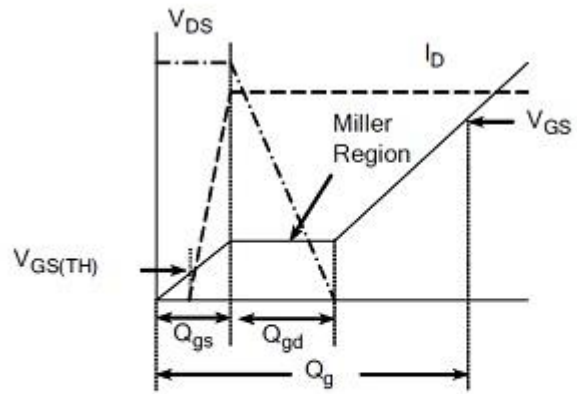


**Figure10. Maximum Continuous Drain Current
versus Case Temperature**

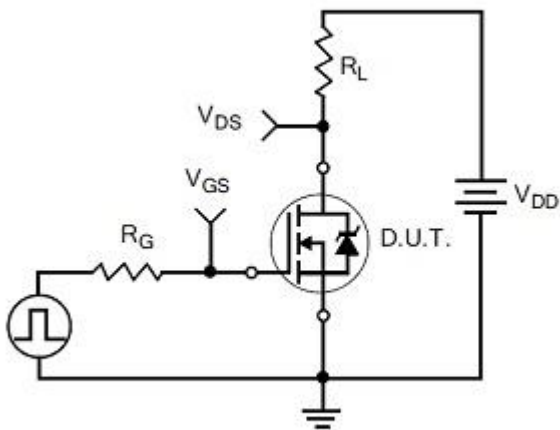
TEST CIRCUITS AND WAVEFORMS



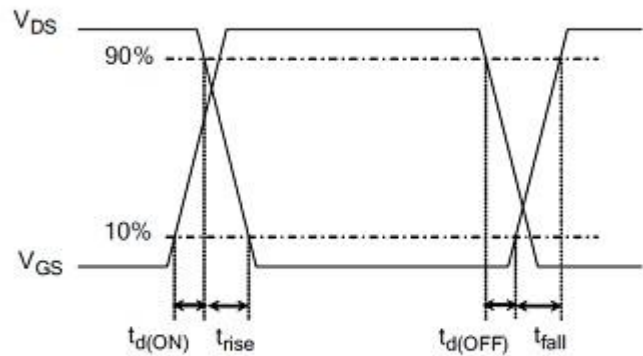
Gate Charge Test Circuit



Gate Charge Waveform

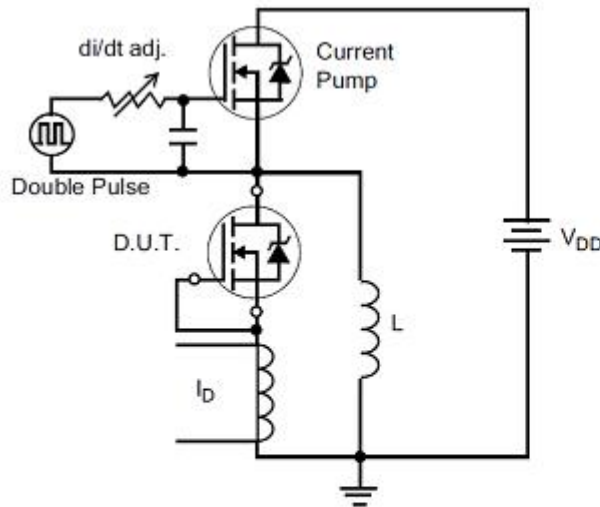


Resistive Switching Test Circuit

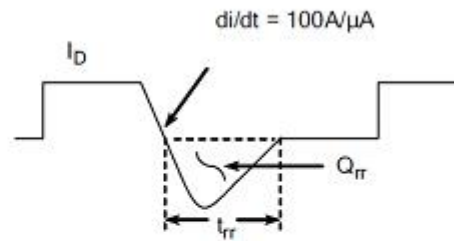


Resistive Switching Waveforms

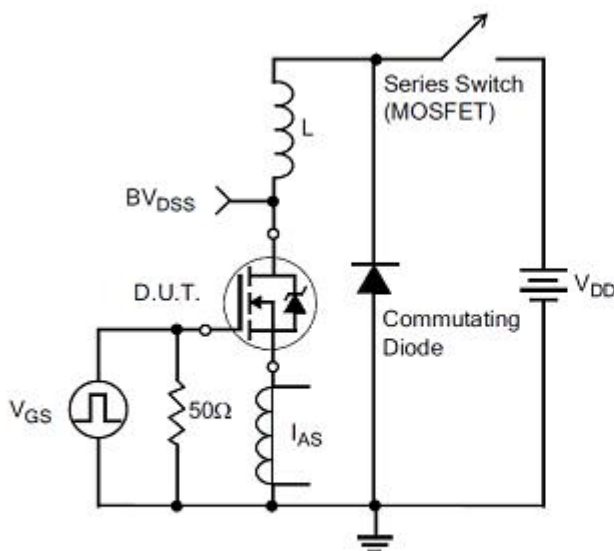
TEST CIRCUITS AND WAVEFORMS(Cont.)



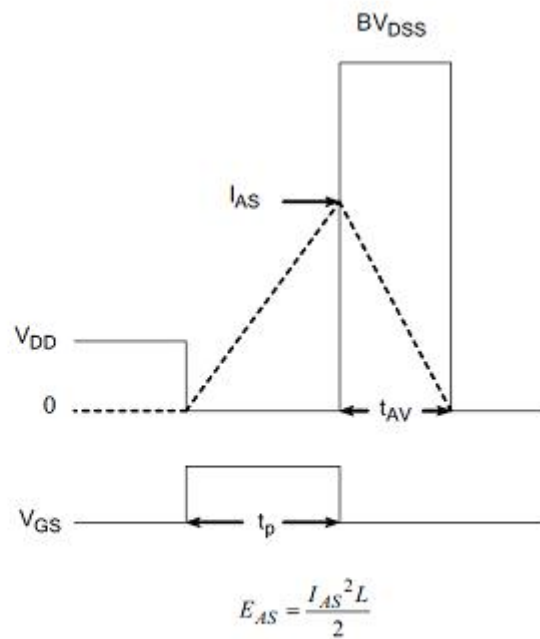
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

Revision history

Document revision history

Date	Revision	Changes
26-Oct-2021	1.0	First release
4-Jan-2022	1.1	Update parameter

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